

Docket No.: 198786US-2RE

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION: Mitsuhiro YANO, et al.

SERIAL NO.: 09/891,925

GAU: 2811

FILED: June 27, 2001

EXAMINER: HU, S.

FOR: SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING SAME

**LETTER SUBMITTING REPLACEMENT DRAWING SHEET(S)**

COMMISSIONER FOR PATENTS  
Alexandria, VA 22313

SIR:

Responsive to the below indicated communication, the following drawing sheets are submitted herewith:

☒ 2 Replacement Drawing Sheets ☐ \_\_\_\_\_ New Drawing Sheets  
☐ \_\_\_\_\_ Annotated Drawing Sheets

☒ Official Action dated May 29, 2008  
☐ Notice of Allowance/Issue Fee dated \_\_\_\_\_  
☐ Other dated \_\_\_\_\_

The changes and/or modifications made include the following:

The original labeled element 16 under the gate layer 17 in Figure 2 is now newly labeled element 161, and is noted in the amended specification as formed of silicon oxide. Figure 8 is also herein amended to consistently refer to elements 8 and 7 and delete the original reference indicator "16".

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.



Gregory J. Maier  
Registration No. 25,599

Customer Number

**22850**

Tel. (703) 413-3000  
Fax. (703) 413-2220  
(OSMMN 06/04)

Surinder Sachar  
Registration No. 34,423